

2N5769



NPN Switching Transistor

This device is designed for high speed saturated switching applications at currents to 100 mA. Sourced from Process 21. See PN2369A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units | |
|-----------------------------------|--------------------------------------------------|-------------|-------|--|
| V_{CEO} | Collector-Emitter Voltage | 15 | V | |
| V _{CBO} | Collector-Base Voltage | 40 | V | |
| V_{EBO} | Emitter-Base Voltage | 4.5 | V | |
| Ic | Collector Current - Continuous | 200 | mA | |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C | |

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | Units |
|-----------------|--------------------------------------------|------------|-------------|
| | | 2N5769 | |
| P _D | Total Device Dissipation Derate above 25°C | 350 2.8 | mW mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 125 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 357 | °C/W |

NPN Switching Transistor (continued)

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|----------------------|--------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------|-------------|----------|
| o== 0 | D.4.075D10710.0 | | | | |
| | RACTERISTICS | T | | | |
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage* | $I_C = 10 \text{ mA}, I_B = 0$ | 15 | | V |
| $V_{(BR)CBO}$ | Collector-Base Breakdown Voltage | $I_C = 10 \mu\text{A}, I_E = 0$ | 40 | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | $I_E = 10 \mu A, I_C = 0$ | 4.5 | | V |
| $V_{(BR)CES}$ | Collector-Emitter Breakdown Voltage | $I_{C} = 10 \mu\text{A}, I_{B} = 0$ | 40 | | V |
| І _{сво} | Collector Cutoff Current | $V_{CB} = 20 \text{ V}, I_{E} = 0$ $V_{CB} = 20 \text{ V}, I_{E} = 0, T_{A} = 125 ^{\circ}\text{C}$ | | 0.4 30 | μA μA |
| I _{CES} | Collector Cutoff Current | $V_{CE} = 20 \text{ V}, I_{B} = 0$ | | 0.4 | μΑ |
| I _{EBO} | Emitter Cutoff Current | $V_{EB} = 4.5 \text{ V}, I_{C} = 0$ | | 1.0 | μΑ |
| ĴFE | DC Current Gain | $I_C = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $T_A = -55 ^{\circ}\text{C}$ $I_C = 30 \text{ mA}, V_{CE} = 0.40 \text{ V}$ | 40 20 30 | 120 | |
| | | | 20 | | |
| | | $I_C = 30 \text{ mA}, V_{CE} = 0.40 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ | 30 20 | | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ | | 0.2 | V |
| | | T _A = 125 °C | | 0.3 | V |
| | | $I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$ | | 0.25 0.5 | V V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ | 0.7 | 0.85 | V |
| | | $T_A = 125 ^{\circ}\text{C}$ $I_C = 10 \text{mA}, I_B = 1.0 \text{mA}$ | 0.59 | 1.02 | V |
| | | T _A = - 55 °C | 0.59 | 1.02 | V |
| | | $I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$ | | 1.15 | V V |
| | IGNAL CHARACTERISTICS | I _C = 100 mA, I _B = 10 mA | | 1.6 | l v |
| C _{cb} | Collector-Base Capacitance | V _{CB} = 5.0 V, f = 1.0 MHz | | 4.0 | pF |
| h _{fe} | Small-Signal Current Gain | $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz | 5.0 | | |
| SWITCHI | NG CHARACTERISTICS | | | | |
| ton | Turn-on Time | I _C = 10 mA, | | 12 | ns |
| t _{off} | Turn-off Time | $I_{B1} = 3.0 \text{ mA}, I_{B2} = 1.5 \text{ mA}$ | | 18 | ns |
| | Storage Time | $I_C = I_{B1} = I_{B2} = 10 \text{ mA}$ | | | |

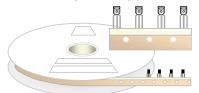
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

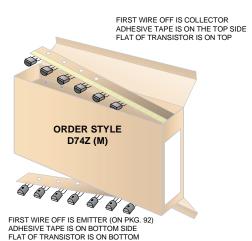


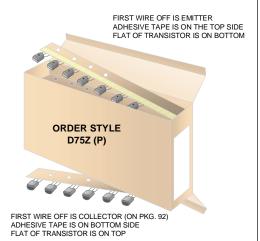
Style "A", D26Z, D70Z (s/h)

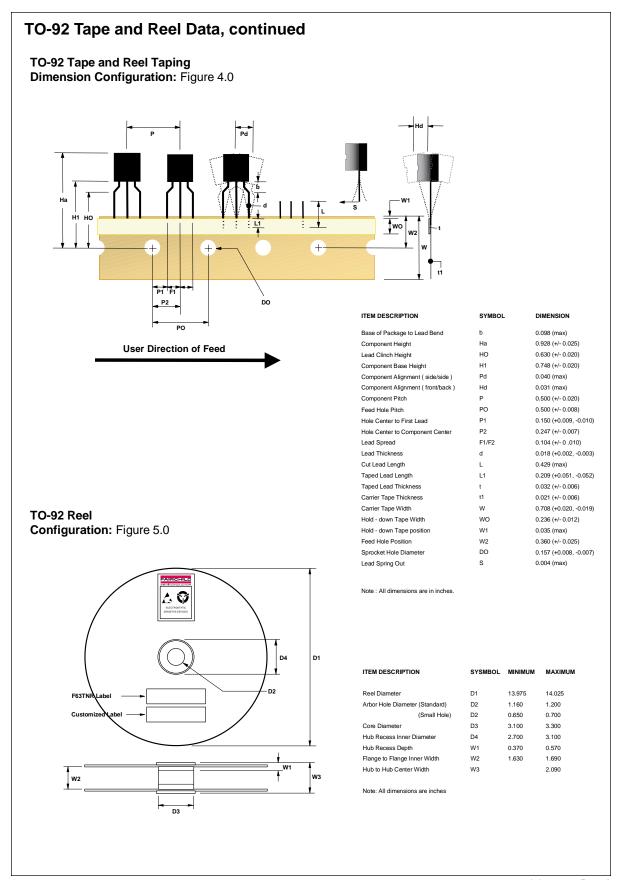
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



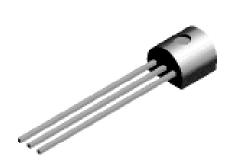


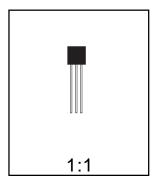


TO-92 Package Dimensions



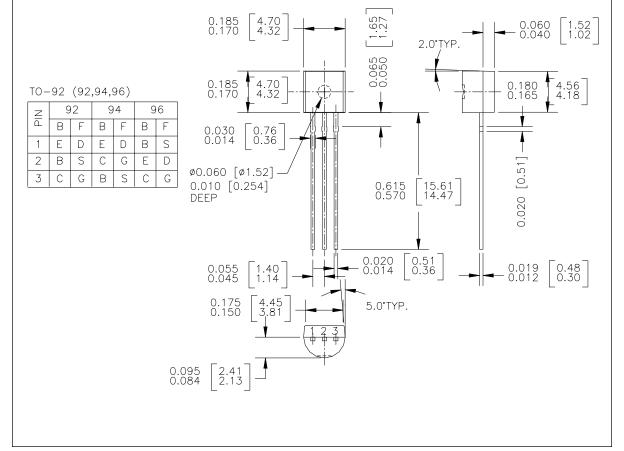
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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